# mail

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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### NPN SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

#### **ISSUE 2 – JULY 1995**

#### FEATURES

- \* 10A Peak pulse current
- \* Excellent h<sub>FF</sub> characteristics up to10A (pulsed)
- \* Extremely low saturation voltage e.g. 7mV typ.
- \* I<sub>C</sub> cont 3.5A

#### APPLICATIONS

 Power MOSFET gate driver in conjunction with complementary ZTX718

#### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	20	V
Collector-Emitter Voltage	V <sub>CEO</sub>	20	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Peak Pulse Current	I <sub>CM</sub>	10	А
Continuous Collector Current	I <sub>C</sub>	3.5	А
Base Current	I <sub>B</sub>	500	mA
Practical Power Dissipation*	P <sub>totp</sub>	1.5	W
Power Dissipation	P <sub>tot</sub>	1	W
Operating and Storage Temperature Range	T <sub>j</sub> :T <sub>stg</sub>	-55 to +200	°C

\* Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.







## ZTX618

#### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.	
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	20	100		V	I <sub>C</sub> =100μA	
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	20	27		V	I <sub>C</sub> =10mA*	
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	5	8.3		V	I <sub>E</sub> =100μA	
Collector Cut-Off Current	I <sub>CBO</sub>			100	nA	V <sub>CB</sub> =16V	
Emitter Cut-Off Current	I <sub>EBO</sub>			100	nA	V <sub>EB</sub> =4V	
Collector Emitter Cut-Off Current	I <sub>CES</sub>			100	nA	V <sub>CES</sub> =16V	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		7 80 210	15 150 255	mV mV mV	I <sub>C</sub> =0.1A, I <sub>B</sub> =10mA* I <sub>C</sub> =1A, I <sub>B</sub> =10mA* I <sub>C</sub> =3.5A, I <sub>B</sub> =50mA*	
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>		0.93	1.05	V	I <sub>C</sub> =3.5A, I <sub>B</sub> =50mA*	
Base-Emitter Turn-On Voltage	V <sub>BE(on)</sub>		0.86	1.0	V	I <sub>C</sub> =3.5A, V <sub>CE</sub> =2V*	
Static Forward Current Transfer Ratio	h <sub>FE</sub>	200 300 170 40	400 450 300 85			$\begin{array}{l} I_{C} = 10 \text{mA}, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} = 200 \text{mA}, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} = 3 \text{A}, \ V_{CE} = 2 \text{V}^{*} \\ I_{C} = 10 \text{A}, \ V_{CE} = 2 \text{V}^{*} \end{array}$	
Transition Frequency	f <sub>T</sub>	100	140		MHz	I <sub>C</sub> =50mA, V <sub>CE</sub> =10V f=100MHz	
Output Capacitance	C <sub>obo</sub>		23	30	pF	V <sub>CB</sub> =10V, f=1MHz	
Turn-On Time	t <sub>(on)</sub>		170		ns	V <sub>CC</sub> =10V, I <sub>C</sub> =1A I <sub>B1</sub> =-I <sub>B2</sub> =10mA	
Turn-Off Time	t <sub>(off)</sub>		400		ns		

\*Measured under pulsed conditions. Pulse width= $300\mu$ s. Duty cycle  $\leq 2\%$ 

**ZTX618** 

#### **TYPICAL CHARACTERISTICS**



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#### THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient <sub>1</sub> Junction to Ambient <sub>2</sub>	$R_{th(j-amb)1} \ R_{th(j-amb)2} \dagger$	175 116	°C/W °C/W

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.





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